

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- SGS-THOMSON PREFERRED SALESTYPES
- COMPLEMENTARY PNP - NPN DEVICES
- MONOLITHIC DARLINGTON CONFIGURATION
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

APPLICATION

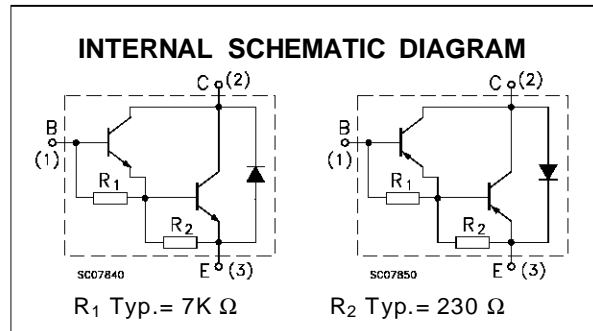
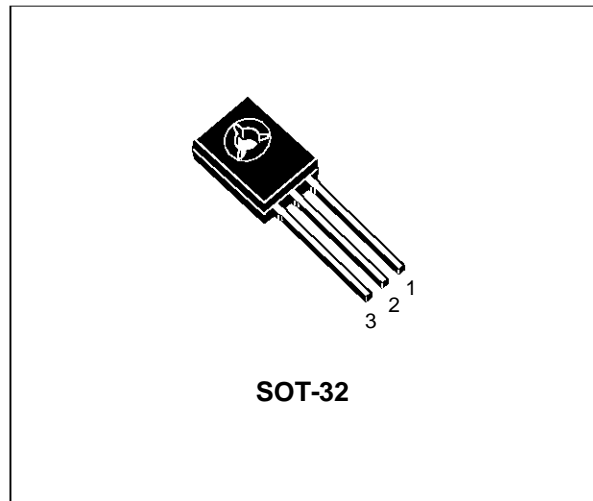
- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

DESCRIPTION

The BD677, BD677A, BD679, BD679A and BD681 are silicon epitaxial-base NPN power transistors in monolithic Darlington configuration mounted in Jedec SOT-32 plastic package.

They are intended for use in medium power linear and switching applications

The complementary PNP types are BD678, BD678A, BD680, BD680A and BD682 respectively.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit	
		NPN	BD677/A	BD679/A		BD681
		PNP	BD678/A	BD680/A		BD682
V_{CBO}	Collector-Base Voltage ($I_E = 0$)		60	80	100	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		60	80	100	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)		5			V
I_C	Collector Current		4			A
I_{CM}	Collector Peak Current		6			A
I_B	Base Current		0.1			A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$		40			W
T_{stg}	Storage Temperature		-65 to 150			$^\circ C$
T_j	Max. Operating Junction Temperature		150			$^\circ C$

For PNP types voltage and current values are negative.

BD677/677A/678/678A/679/679A/680/680A/681/682

THERMAL DATA

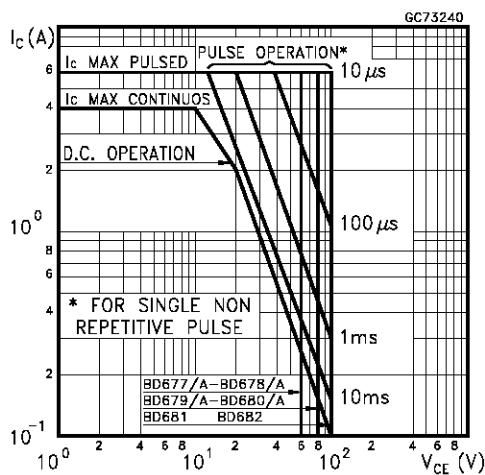
R _{thj-case}	Thermal Resistance Junction-case	Max	3.12	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	100	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

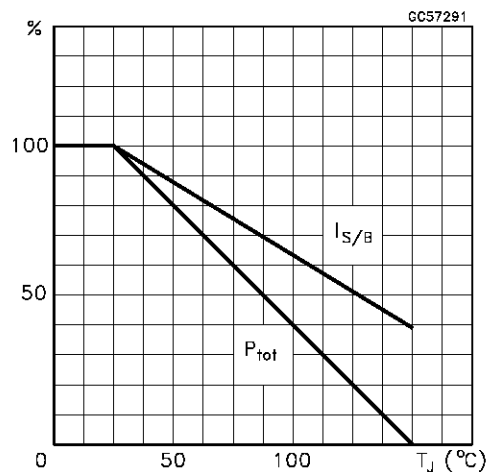
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CE} = rated V _{CBO} V _{CE} = rated V _{CBO} T _C = 100 °C			0.2 2	mA mA
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = half rated V _{CEO}			0.5	mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			2	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage	I _C = 50 mA for BD677/677A/678/678A for BD679/679A/680/680A for BD681/682	60 80 100			V V V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	for BD677/678/679/680/681/682 I _C = 1.5 A I _B = 30 mA for BD677A/678A/679A/680A I _C = 2 A I _B = 40 mA			2.5 2.8	V V
V _{BE*}	Base-Emitter Voltage	for BD677/678/679/680/681/682 I _C = 1.5 A V _{CE} = 3 V for BD677A/678A/679A/680A I _C = 2 A V _{CE} = 3 V			2.5 2.5	V V
h _{FE*}	DC Current Gain	for BD677/678/679/680/681/682 I _C = 1.5 A V _{CE} = 3 V for BD677A/678A/679A/680A I _C = 2 A V _{CE} = 3 V	750 750			
h _{fe}	Small Signal Current Gain	I _C = 1.5 A V _{CE} = 3 V f = 1MHz	1			

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

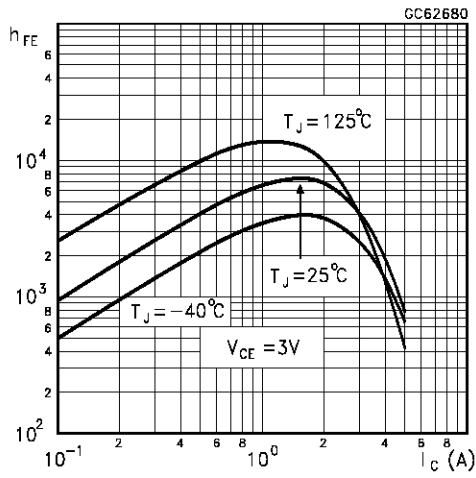
Safe Operating Areas



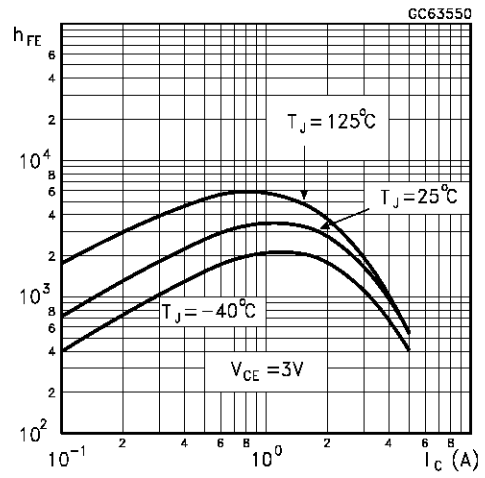
Derating Curve



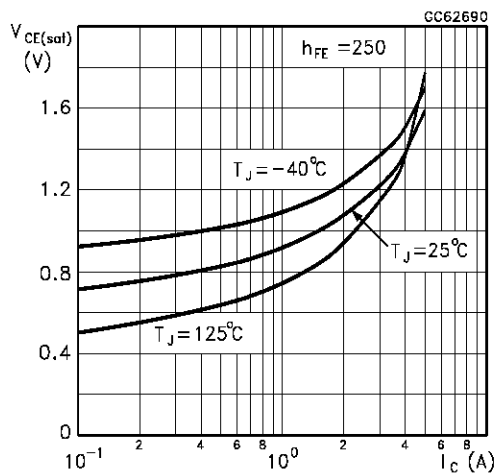
DC Current Gain (NPN type)



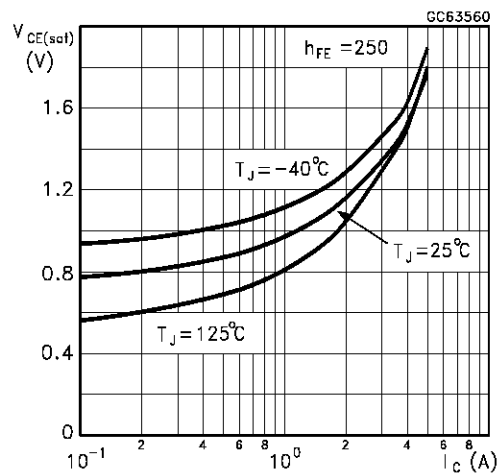
DC Current Gain (PNP type)



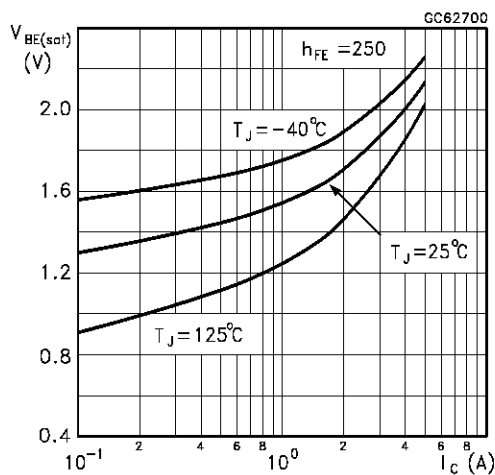
Collector-Emitter Saturation Voltage (NPN type)



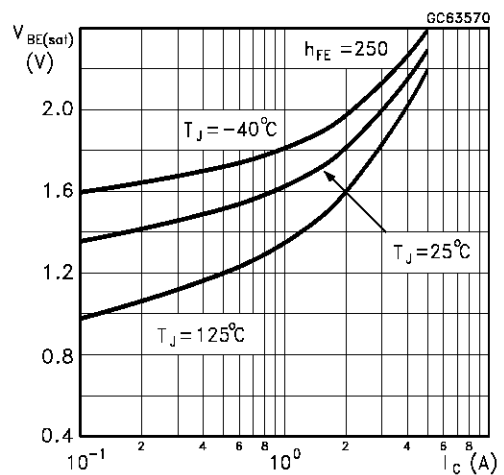
Collector-Emitter Saturation Voltage (PNP type)



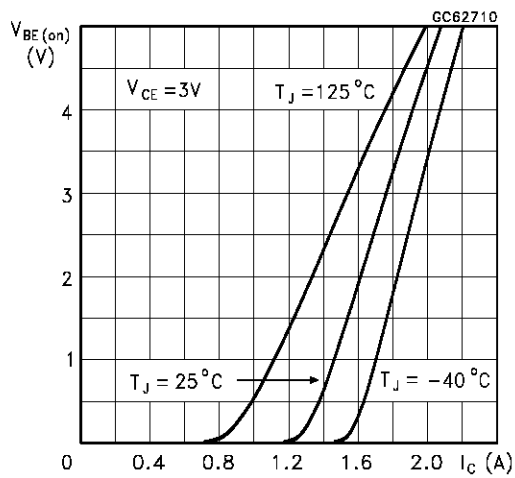
Base-Emitter Saturation Voltage (NPN type)



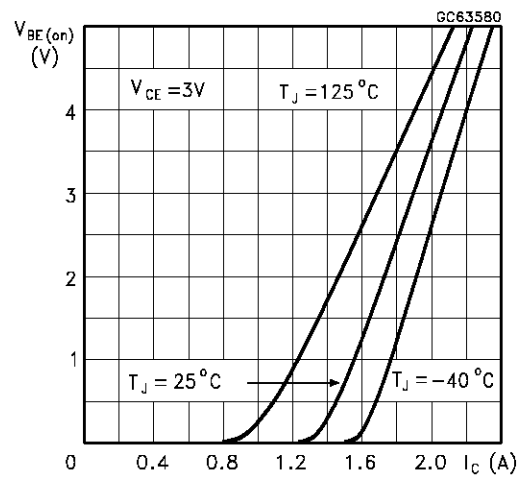
Base-Emitter Saturation Voltage (PNP type)



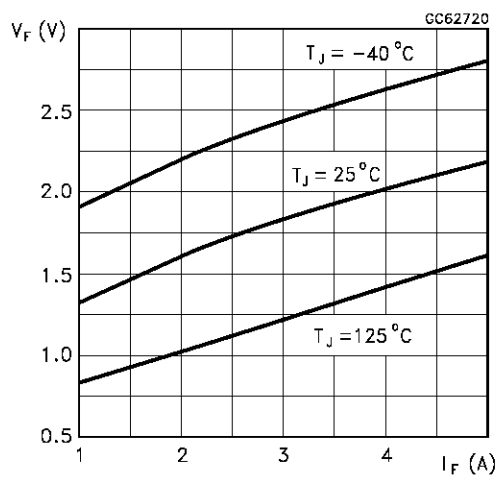
Base-Emitter On Voltage (NPN type)



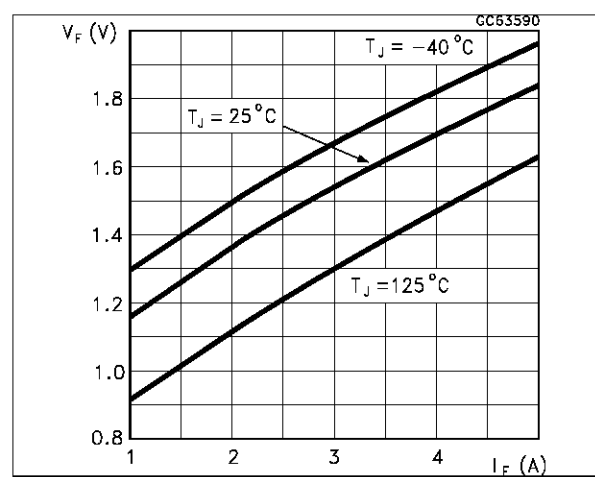
Base-Emitter On Voltage (PNP type)



Freewheel Diode Forward Voltage (NPN types)

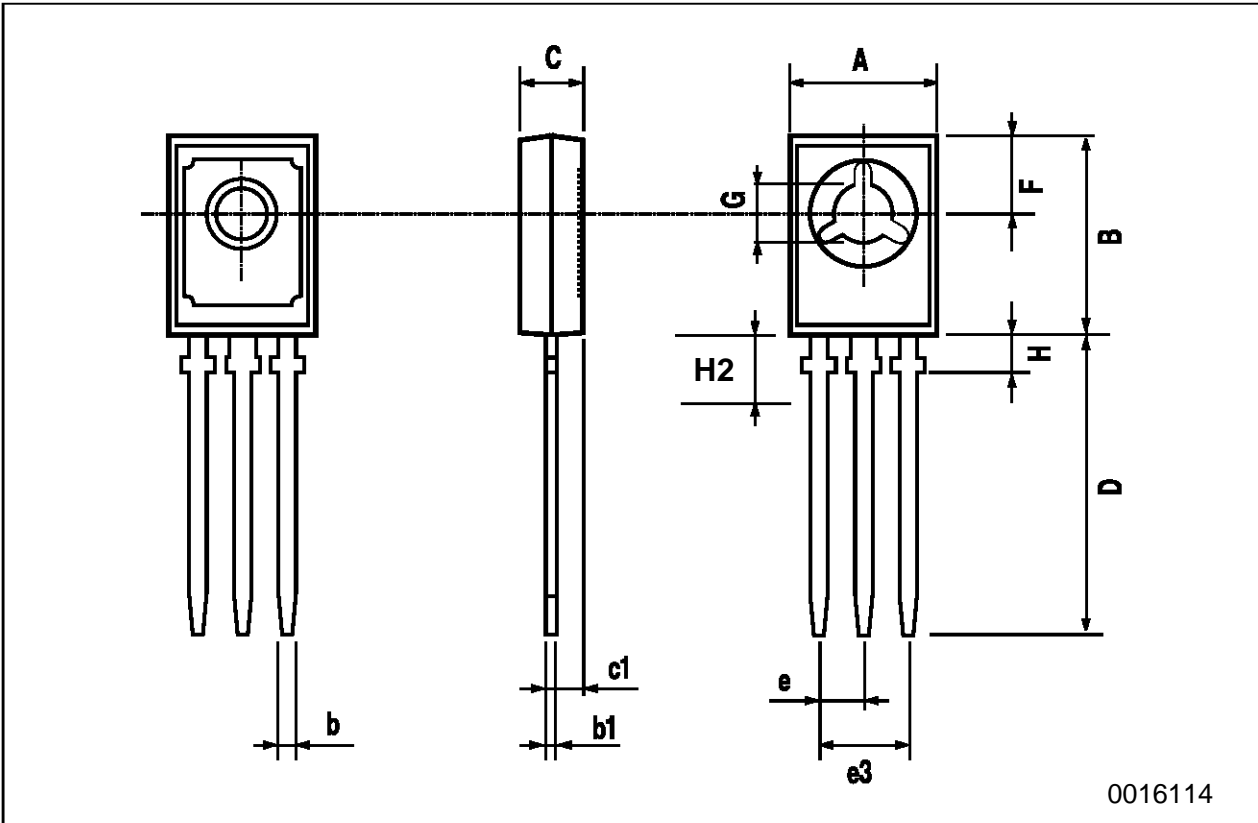


Freewheel Diode Forward Voltage (PNP types)



SOT-32 (TO-126) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	7.4		7.8	0.291		0.307
B	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
C	2.4		2.7	0.040		0.106
c1	1.0		1.3	0.039		0.050
D	15.4		16.0	0.606		0.629
e		2.2			0.087	
e3	4.15		4.65	0.163		0.183
F		3.8			0.150	
G	3		3.2	0.118		0.126
H			2.54			0.100
H2		2.15			0.084	



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Datasheets for electronics components.

BD676, BD676A, BD678, BD678A, BD680, BD680A, BD682



ON Semiconductor®

<http://onsemi.com>

Plastic Medium-Power Silicon PNP Darlington

This series of plastic, medium-power silicon PNP Darlington transistors can be used as output devices in complementary general-purpose amplifier applications.

Features

- Pb-Free Package is Available*
- High DC Current Gain –
 $h_{FE} = 750$ (Min) @ $I_C = 1.5$ and 2.0 Adc
- Monolithic Construction
- BD676, 676A, 678, 678A, 680, 680A, 682 are complementary with BD675, 675A, 677, 677A, 679, 679A, 681
- BD678, 678A, 680, 680A are equivalent to MJE 700, 701, 702, 703

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BD676, BD676A BD678, BD678A BD680, BD680A BD682	V_{CEO}	45 60 80 100	Vdc
Collector-Base Voltage BD676, BD676A BD678, BD678A BD680, BD680A BD682	V_{CB}	45 60 80 100	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current	I_C	4.0	Adc
Base Current	I_B	0.1	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

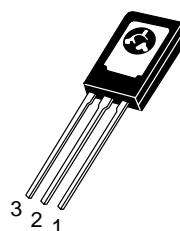
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.13	$^\circ\text{C}/\text{W}$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

4.0 A DARLINGTON POWER TRANSISTORS PNP SILICON 45, 60, 80, 100 V, 40 W



TO-225AA
CASE 77
STYLE 1

MARKING DIAGRAM



xxx = 76, 76A, 78, 78A, 80, 80A or 82
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

BD676, BD676A, BD678, BD678A, BD680, BD680A, BD682

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (Note 1) ($I_C = 50\text{ mAdc}$, $I_B = 0$)	BD676, 676A BD678, 678A BD680, 680A BD682	BV_{CEO}	45 60 80 100	– – – –	Vdc
Collector Cutoff Current ($V_{CE} = \text{Half Rated } V_{CEO}$, $I_B = 0$)		I_{CEO}	–	500	μAdc
Collector Cutoff Current ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$) ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$, $T_C = 100^\circ\text{C}$)		I_{CBO}	– –	0.2 2.0	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)		I_{EBO}	–	2.0	mAdc

ON CHARACTERISTICS

DC Current Gain (Note 1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	BD676, 678, 680, 682 BD676A, 678A, 680A	h_{FE}	750 750	– –	
Collector–Emitter Saturation Voltage (Note 1) ($I_C = 1.5\text{ Adc}$, $I_B = 30\text{ mAdc}$) ($I_C = 2.0\text{ Adc}$, $I_B = 40\text{ mAdc}$)	BD678, 680, 682 BD676A, 678A, 680A	$V_{CE(sat)}$	– –	2.5 2.8	Vdc
Base–Emitter On Voltage (Note 1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	BD678, 680, 682 BD676A, 678A, 680A	$V_{BE(on)}$	– –	2.5 2.5	Vdc

DYNAMIC CHARACTERISTICS

Small–Signal Current Gain ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	h_{fe}	1.0	–	–
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1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

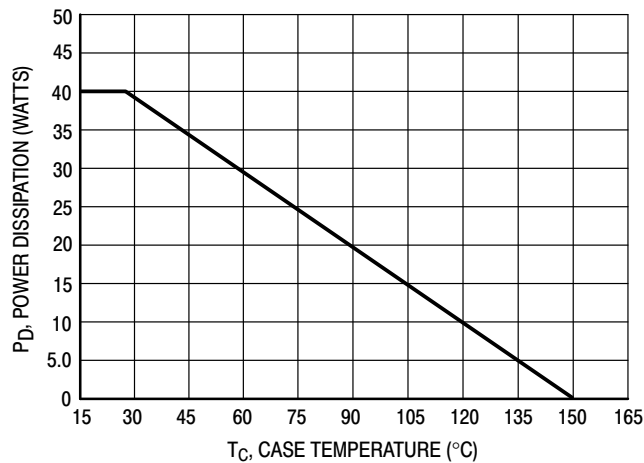


Figure 1. Power Temperature Derating

BD676, BD676A, BD678, BD678A, BD680, BD680A, BD682

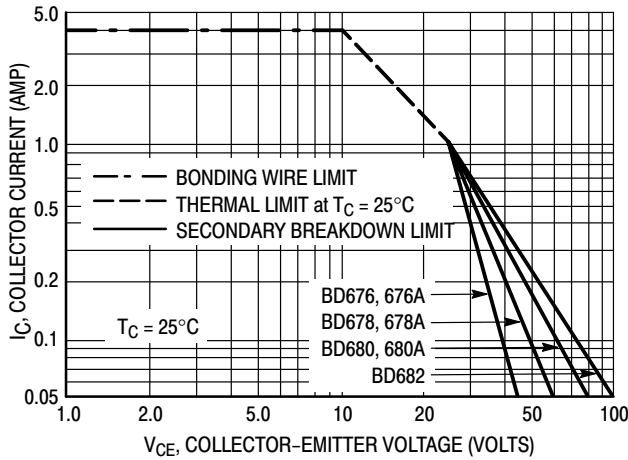


Figure 2. DC Safe Operating Area

There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; e.g., the transistor must not be subjected to greater dissipation than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

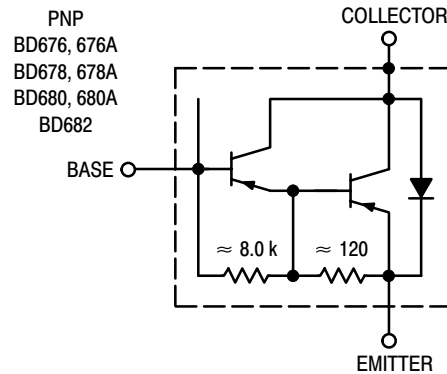


Figure 3. Darlington Circuit Schematic

ORDERING INFORMATION

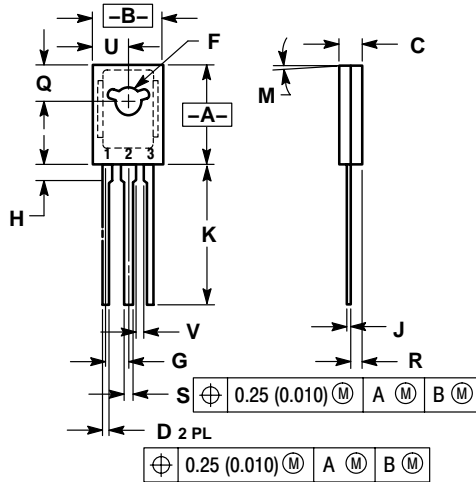
Device	Package	Shipping†
BD676	TO-225AA	500 Units / Box
BD676G	TO-225AA (Pb-Free)	
BD676A	TO-225AA	500 Units / Box
BD678	TO-225AA	500 Units / Box
BD678A	TO-225AA	
BD680	TO-225AA	500 Units / Box
BD680A	TO-225AA	
BD682	TO-225AA	500 Units / Box
BD682G	TO-225AA (Pb-Free)	
BD682T	TO-225AA	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BD676, BD676A, BD678, BD678A, BD680, BD680A, BD682

PACKAGE DIMENSIONS

TO-225AA
CASE 77-09
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:

- PIN 1. EMITTER
- COLLECTOR
- BASE

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Datasheets for electronics components.